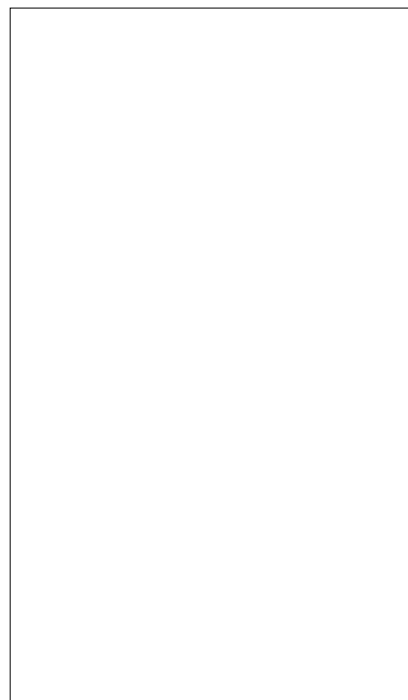




JCT810H 10A SCR

Rev.A.1.1

DESCRIPTION:

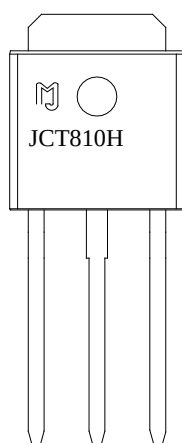


Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-			

ORDERING INFORMATION

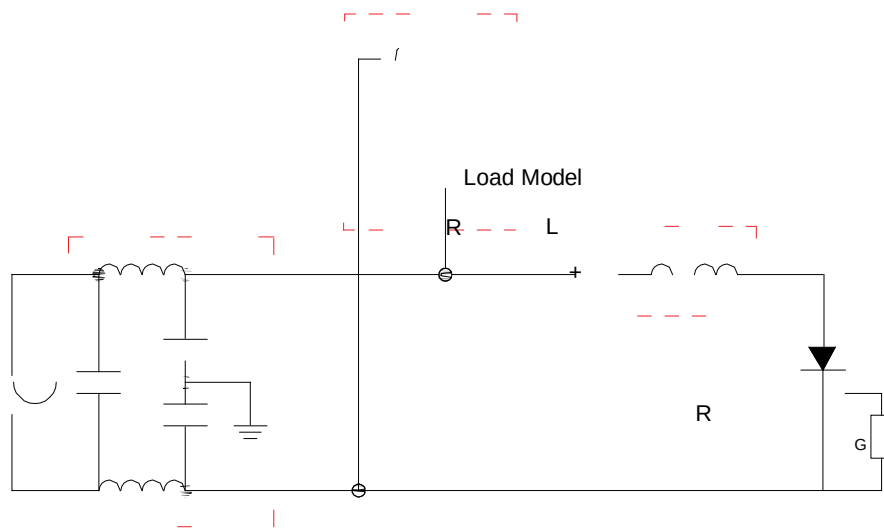
<u>J</u>	<u>CT</u>	<u>8</u>	<u>10</u>	<u>H</u>
JieJie Microelectronics Co., Ltd.	SCRs			H:TO-251
		8:V _{DRM} /V _{RRM} 1800V	I _{T(RMS)} :10A	

MARKING



JCT810H

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package
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